

## N-Channel 100 V (D-S) MOSFET


**Marking Code:** AVXX

PRODUCT SUMMARY	
$V_{DS}$ (V)	100
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.212
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.270
$Q_g$ typ. (nC)	1.86
$I_D$ (A) <sup>a</sup>	2.38
Configuration	Single

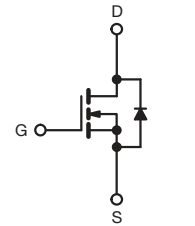
### FEATURES

- TrenchFET® Gen IV power MOSFET
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- Load switches
- DC/DC converters
- Power management
- LED backlighting



N-Channel MOSFET

ORDERING INFORMATION	
Package	SOT-363
Lead (Pb)-free and halogen-free	Si1480BDH-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{DS}$	100	V	
Gate-source voltage	$V_{GS}$	$\pm 20$		
Continuous drain current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_C = 25$ °C	2.38 <sup>a</sup>	A
		$T_C = 70$ °C	1.9	
		$T_A = 25$ °C	1.8 <sup>b, c</sup>	
		$T_A = 70$ °C	1.4 <sup>b, c</sup>	
Pulsed drain current ( $t = 300$ $\mu$ s)	$I_{DM}$	7		
Avalanche current	$I_{AS}$	3	mJ	
Repetitive avalanche energy				
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	2.3	A
		$T_A = 25$ °C	1.3 <sup>b, c</sup>	
Maximum power dissipation <sup>a</sup>	$P_D$	$T_C = 25$ °C	2.6	W
		$T_C = 70$ °C	1.7	
		$T_A = 25$ °C	1.5 <sup>b, c</sup>	
		$T_A = 70$ °C	0.97 <sup>b, c</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b, d</sup>	$R_{thJA}$	62	82	°C/W
Maximum junction-to-foot (drain)	$R_{thJF}$	37	47	

**Notes**

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 5$  s
- Maximum under steady state conditions is 130 °C/W



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	87	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-4.3	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.6	-	3	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A	-	0.176	0.212	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1.5 A	-	0.196	0.270	
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2 A	-	9	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	206	-	pF
Output capacitance	C <sub>oss</sub>		-	24	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	5	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A	-	3.9	6.0	nC
		V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2 A	-	1.86	3.0	
Gate-source charge	Q <sub>gs</sub>		-	0.93	-	
Gate-drain charge	Q <sub>gd</sub>	-	0.5	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.0	3.5	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 25 Ω I <sub>D</sub> ≅ 2 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	11	22	ns
Rise time	t <sub>r</sub>		-	25	50	
Turn-off delay time	t <sub>d(off)</sub>		-	10	20	
Fall time	t <sub>f</sub>		-	12	24	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 25 Ω I <sub>D</sub> ≅ 2 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	6	12	ns
Rise time	t <sub>r</sub>		-	4	8	
Turn-off delay time	t <sub>d(off)</sub>		-	10	20	
Fall time	t <sub>f</sub>		-	3	6	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	2.3	A
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>		-	-	7	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 2 A, V <sub>GS</sub> = 0 V	-	0.85	1.2	V
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 2 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	22	44	nC
Body diode reverse recovery time	t <sub>rr</sub>		-	20	40	
Reverse recovery fall time	t <sub>a</sub>		-	18	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	3	-	

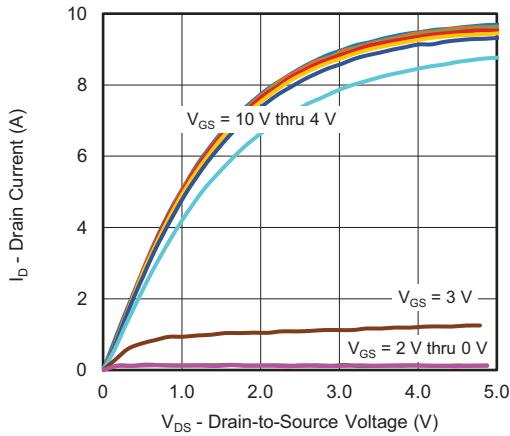
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing

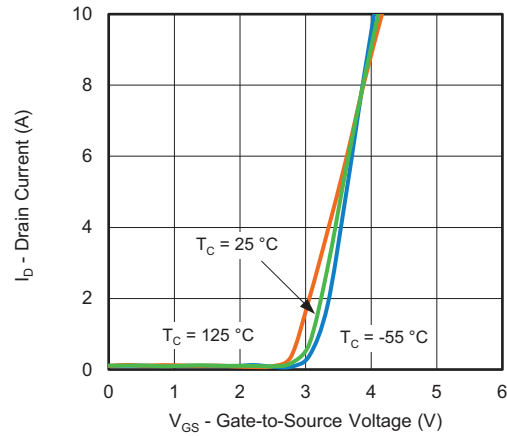
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



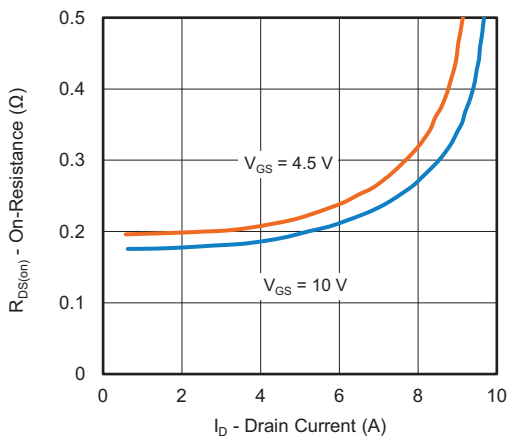
TYPICAL CHARACTERISTICS (T<sub>A</sub>= 25 °C, unless otherwise noted)



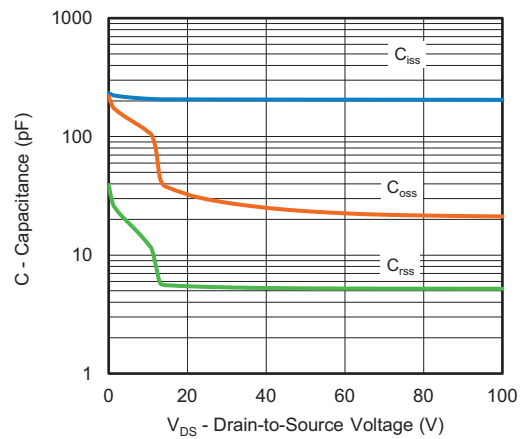
Output Characteristics



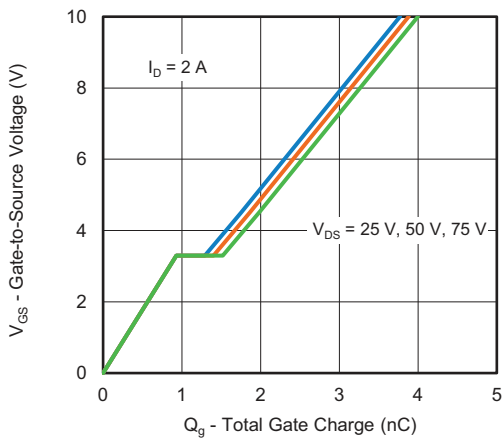
Transfer Characteristics Curves vs. Temperature



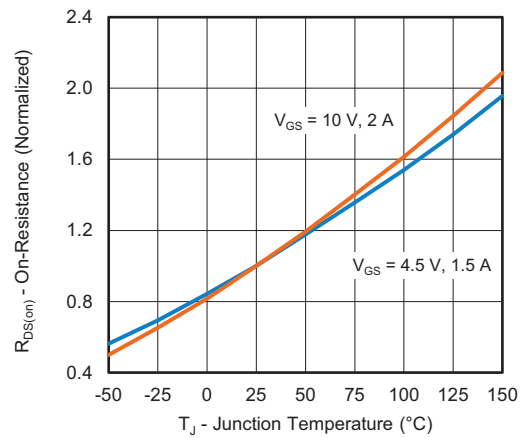
On-Resistance vs. Drain Current



Capacitance



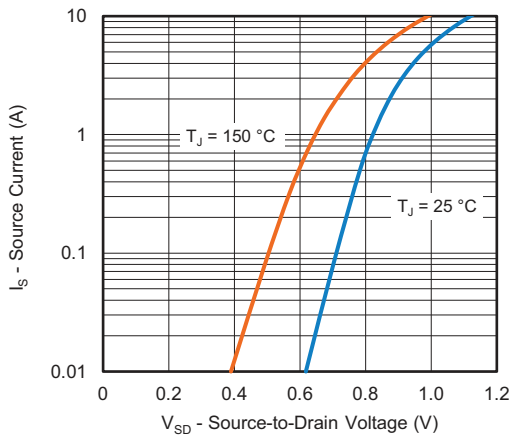
Gate Charge



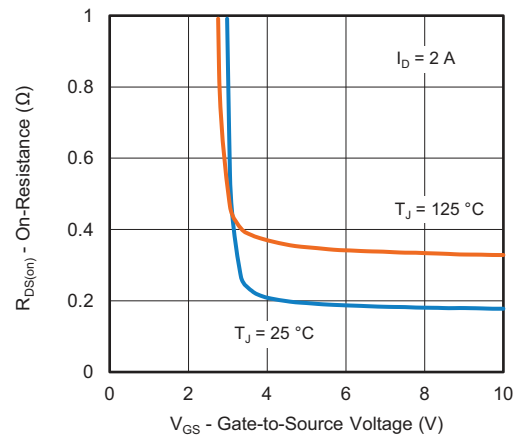
On-Resistance vs. Junction Temperature



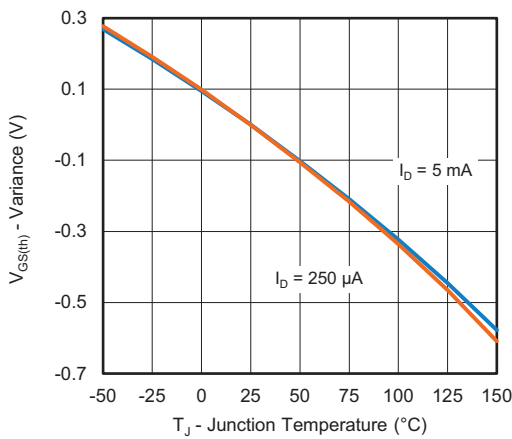
TYPICAL CHARACTERISTICS (T<sub>A</sub>= 25 °C, unless otherwise noted)



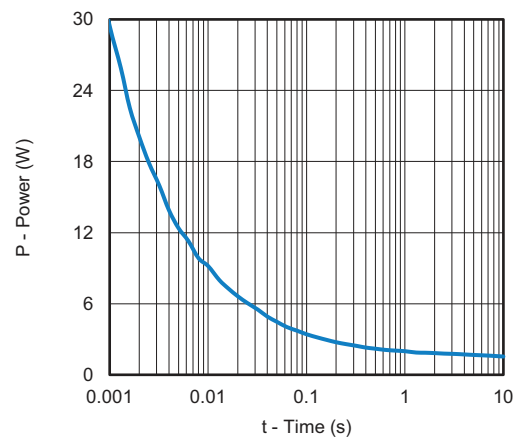
Source-Drain Diode Forward Voltage



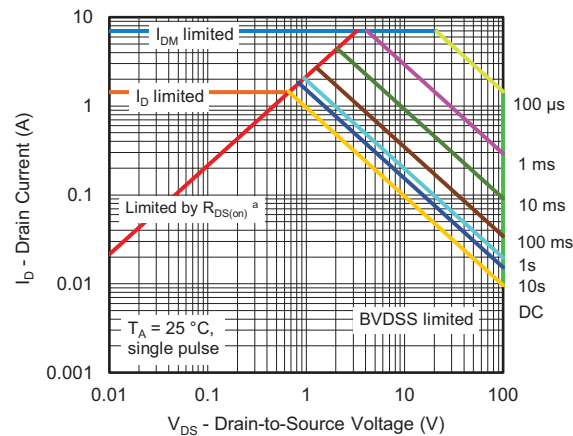
R<sub>DS(on)</sub> vs. V<sub>GS</sub> vs. Temperature



Threshold Voltage



Single Pulse Power



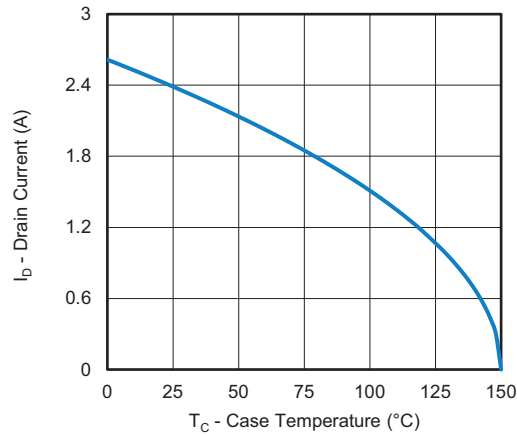
Safe Operating Area, Junction-to-Ambient

Note

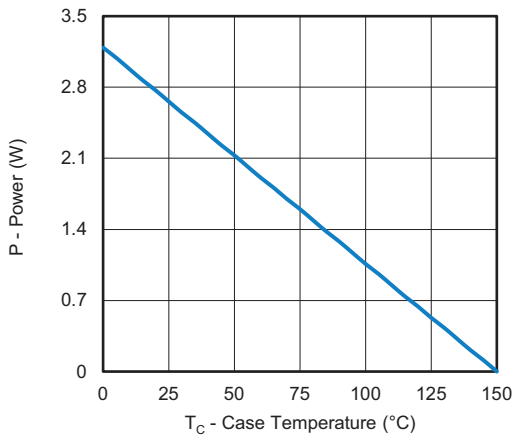
a. V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified



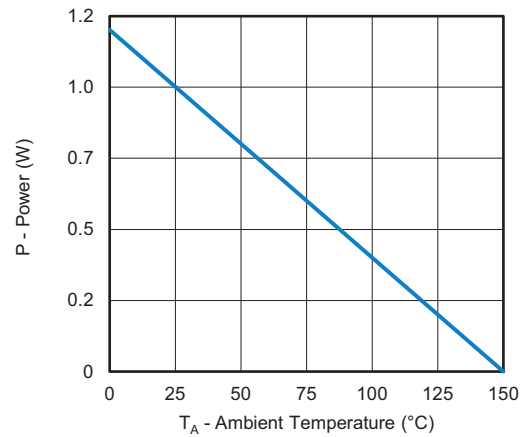
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Case**



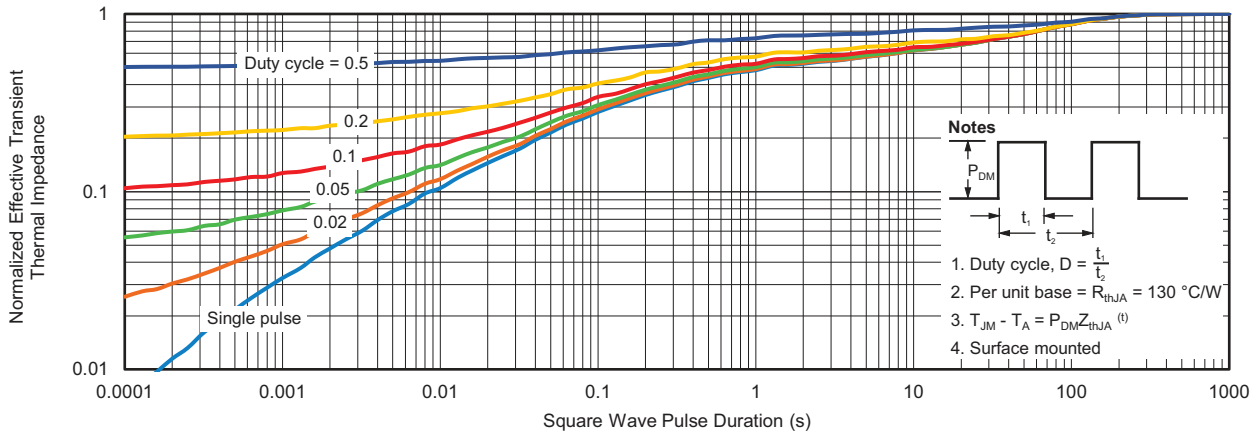
**Power, Junction-to-Ambient**

**Note**

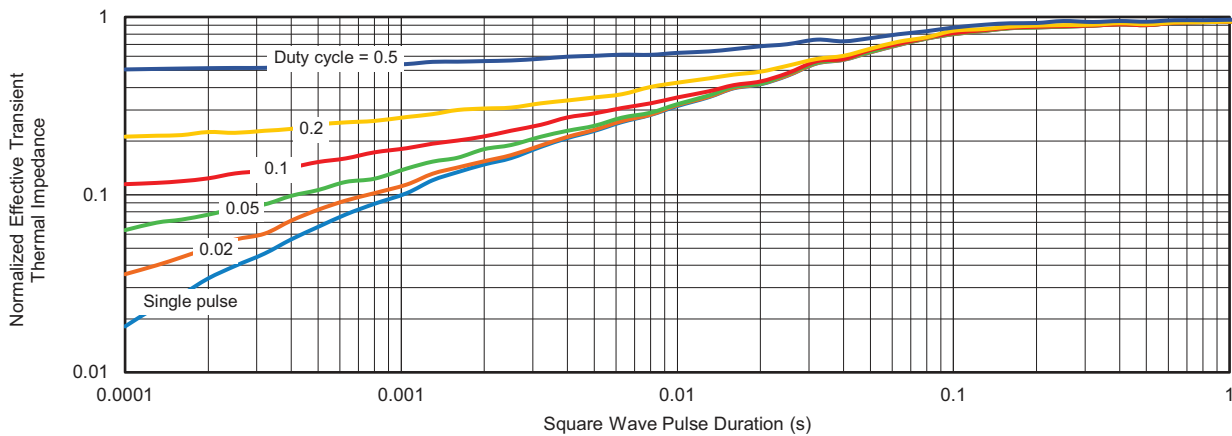
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150  $^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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